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# Gallium Nitride and Silicon Carbide Power Technologies

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Published by

**The Electrochemical Society**

65 South Main Street, Building D  
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

[www.electrochem.org](http://www.electrochem.org)

**ecstransactions**™

**Vol. 41, No. 8**

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Published by:

The Electrochemical Society  
65 South Main Street  
Pennington, New Jersey 08534-2839, USA

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e-mail: [ecs@electrochem.org](mailto:ecs@electrochem.org)  
Web: [www.electrochem.org](http://www.electrochem.org)

ISSN 1938-6737 (online)  
ISSN 1938-5862 (print)  
ISSN 2151-2051 (cd-rom)

ISBN 978-1-56677-908-1 (Hardcover)  
ISBN 978-1-60768-262-2 (PDF)

Printed in the United States of America.

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